LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
E	Change to vendor similar part number for vendor CAGE number 61772 for devices OBKX, O9KX, 10KX, 11KX, 12KX, 13KX, 14KX, 15KX, and 16KX. Remove vendor CAGE number 61772 from devices OBYX, O9YX, 10YX, 11YX, 12YX, 13YX, 15YX, and 16YX. Change to vendor similar part number for vendor CAGE number 65786 for devices O9 and 11. Add vendor CAGE number 50088 to the drawing as a source of supply for devices O4JX and O5JX. Add vendor CAGE number 65896 to the drawing as a source of supply for devices 15 and 16. Removed 4.3.3 from drawing. Editorial changes thoughout.	92-04-27	W.O.

THE ORIGINAL FIRST PAGE OF THIS DRAWING HAS BEEN REPLACED.

CURRENT	CAG	E CC	DDE	6726	8														
REV																			
SHEET																			
REV	E	E	E	E	E	E	E	Е	E	Ε	E								
SHEET	14	15	16	17	18	19	20	21	22	23	24								
REV STATUS			RE	v		E	E	E	E	D	E	E	Е	Ε	E	E	E	E	
OF SHEET	S			SH	EET		1	2	3	4 5 6 7 8 9 10 11 12				13					
PMIC N/A					ARED E es E.	Y Jamisc	on			DEFENSE ELECTRONICS SUPPLY CENTER									
	ITAI	RY	•		KED BY Monni					DAYTON, OHIO 45444						<del></del>			
DRAWING  THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS				APPROVED BY Don Cool					MICROCIRCUITS, MEMORY, DIGITAL, CMOS, 16K (2048 X 8) BIT STATIC RAM, MONOLITHIC SILICON										
AND AGE	CIES C	OF THE		DRAW		PROVAL													
AMSC N//	4			REVI	SION L		SIZE CAGE CODE 8403 VEL E A 14933				36								

SHEET

OF

24

DESC FORM 193-1

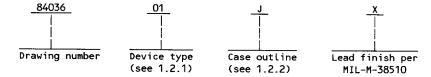
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DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

5962-E262

### 1. SCOPE

- 1.1 <u>Scope</u>. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-Jan devices".
  - 1.2 Part or Identifying Number (PIN). The complete PIN shall be as shown in the following example:



1.2.1 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

Device type	Generic number	1/	Supply voltage variation	<u>A</u>	ddress access time
01			10%	200 n	s (synchronous)
02			10%	90 n	
03			10%	90 n	S
04			10%	150 n	S
05			10%	200 n	S
06			10%	70 n	S
07			10%	120 n	s (synchronous)
08			10%	45 n	
09			10%	45 n	S
10			10%	55 n	S
11			10%	55 n	3
12			10%	70 n	- 3
13			10%	70 n	5
14			10%	35 n	
15			10%	120 n	3
16			10%	90 n	

1.2.2 <u>Case outline(s)</u>. The case outline(s) shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter	Case outline
J	D-3 (24-lead, 1.290" x .610" x .225"), dual-in-line package
K	F-6 (24-lead, .640" x .420" x .090"), flat package
L	D-9 (24-lead, 1.280" x .310" x .200"), dual-in-line package
X	C-12 (32-terminal, .560" x .458" x .120"), rectangular chip carrier package
Υ	Figure 1, (24-lead, .308" x .408"), rectangular chip carrier package
Z	C-12 (32-terminal, .560" x .458" x .120"), rectangular chip carrier package with castellated instead of chamfered corners and extended pad metallization at terminal number 1.
3	C-4 (28-terminal, .460" x .460" x .100"), square chip carrier package

Generic numbers are listed on the standardized military drawing source approval bulletin at the end of this document and will also be listed in MIL-BUL-103.

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1.3	Absolute maximum ratings.			
	Supply voltage range ( $V_{CC}$ )	55°C to + 1.0 W +275°C - See MIL-M 30°C/W +150°C <u>3</u> /	-150°C -38510, appendix C	
1.4	Recommended operating conditions.		•	
2.1	Case operating temperature range $(T_C)$ Input low voltage $(V_{IL})$ :  Device types 01 through 16 Input high voltage $(V_{IH})$ :  Device types 01, 07 Device types 02 through 06, 08 through 16 Supply voltage range $(V_{CC})$ : Minimum chip enable low time Minimum chip enable high time Maximum input rise time Maximum input fall time	0.3 V dc 2.4 V dc t 2.2 V dc t 4.5 V dc t 40 ns 5/ 40 ns 5/ 40 ns 40 ns	to 0.8 V dc 2/ co V <sub>CC</sub> +0.3 V dc 2/ co V <sub>CC</sub> +0.3 V dc 2/ co 5.5 V dc 2/	
	of Specifications and Standards specified in the sol tent specified herein.	icitation, form a	a part of this drawing to	
SPEC	IFICATION			
MI	LITARY			
	MIL-M-38510 - Microcircuits, General Specif	ication for.		
STAN	DARD			
MI	LITARY			
	MIL-STD-883 - Test Methods and Procedures f	or Microelectroni	ics.	
BULL	ETIN			
MI	LITARY			
	MIL-BUL-103 - List of Standardized Military	Drawings (SMD's)	).	
(Cop acquis	ies of the specification, standard, and bulletin req ition functions should be obtained from the contract	uired by manufact ing activity or a	curers in connection with as directed by the contrac	specific ting activity.)
3/ Ma co 4/ Ne	l voltages referenced to V <sub>SS</sub> . ximum junction temperature shall not be exceeded exc nditions in accordance with method 5004 of MIL-STD-8 gative undershoots to a minimum of -3.0 V are allowe r device types 02, 03, and 06 only.	83.		creening
1	STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		84036
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2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

### REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
  - 3.2.1 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.2 herein.
  - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 2.
  - 3.2.3 <u>Truth table</u>. The truth table shall be as specified on figure 3.
  - 3.2.4 Block diagram. The block diagrams shall be as specified on figure 4.
- 3.2.5 <u>Die overcoat</u>. Polyimide and silicone coatings are allowable as an overcoat on the die for alpha particle protection provided that each coated microcircuit inspection lot (see MIL-M-38510) shall be subjected to and pass the internal moisture content test (method 1018 of MIL-STD-883), the frequency of the internal water vapor testing may not be decreased unless approved by the preparing activity.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.
- 3.5 <u>Marking</u>. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103 (see 6.6 herein).
- 3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.6 herein). The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.9 <u>Verification and review</u>. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

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Test	Symbol	Conditions 1/2/	Group A	Device	Limit	s	Unit
		V <sub>SS</sub> = 0 V, 4.5 V ≤ V <sub>C</sub> C ≤ 5.5 V -55°C ≤ T <sub>C</sub> ≤ +125°C unless otherwise specified	subgroups   	types	Min	   Max	
High level output voltage	v <sub>oH</sub>	I <sub>OH</sub> = -1 mA	1, 2, 3	01-07, 15,16	2.4		   <b>V</b> 
		$I_{OH} = -4 \text{ mA}$	 	08-14			
Low level output voltage	v <sub>oL</sub>	I <sub>OL</sub> = 3.2 mA	1, 2, 3	01,07	    -	0.4	   <b>v</b> 
		I <sub>OL</sub> = 4.0 mA	-	02,03, 06,15			
		I <sub>OL</sub> = 2.0 mA		04,05,16			    -
		I <sub>OL</sub> = 8.0 mA	   	08-14			   
High impedance output	   I <sub>OL</sub> Z	OE = V <sub>IH</sub>	1, 2, 3	01,02 06,07	-1.0	1.0	   µА
leakage current	IOHZ			04,05,09,  11,13,14,   15,16	-10.0	10.0	   
				03,08,	_5.0	5.0	
Input leakage current	IIL	  V <sub>IN</sub> = GND  V <sub>IN</sub> = 5.5 V	1, 2, 3	01,02, 06,07 04,05,15	-1.0 -2.0	1.0	   μ <b>Α</b>
				03,08,10, 12,16 09,11,	   -5.0 	5.0	   
Operating supply				13,14	-10.0 	10.0	<u> </u>
current	I <sub>CC1</sub>	$ V_{CC}  = 5.5 \text{ V, f} = \text{fmax}  \underline{3}/$ $ \underline{CE}  = V_{TL}, \text{ outputs open}$	1, 2, 3	01,07 04,05,13, 15,16	<u> </u>   	10	<b>mA</b>   
		CE = V <sub>IL</sub> , outputs open  All other inputs at V <sub>IL</sub>		02,03,06		70	i i
		 		08,10,12		85	
		1		   <u>09,11</u>		120	 
			<u> </u>	14		  150	
Standby supply current	I <sub>CC2</sub>	CE = WE = V <sub>IH</sub> , I <sub>O</sub> = 0	1, 2, 3	02,03,06 04,05 10,12,	 	8 10	   mA 
		 		<u>15,16</u>   09,11,   13,14		15     25	 

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Test	  Symbol	   Conditions <u>1</u> / <u>2</u> /	  Group A	Device		Limits	
		$V_{SS} = 0 \text{ V}, 4.5 \text{ V} \leq V_{CC} \leq 5.5 \text{ V}$ -55°C $\leq T_{C} \leq +125$ °C unless otherwise specified	subgroups	types	Min	   Max 	   
Standby supply current	I <sub>CC3</sub>	CE = V <sub>CC</sub> -0.3 V, I <sub>O</sub> = 0	1, 2, 3	06,07	<u> </u> 	50	   μΑ
our one				01,02	<u> </u>	100	
		 	<u> </u>   	04,05 03,08,10,	<u> </u> 	250	 
				12,15,16	<u> </u>	900	
				13	<u> </u>	10	mA
			ļ	09,11,14	<u> </u>	20	mA
Data retention supply current	I <sub>cc4</sub>	$\frac{1}{CE} = V_{CC}, V_{CC} = 2.0 \text{ V}$	  1, 2, 3 	01,02	 	50	   μ <b>Α</b>
11 7	į			04,05	<u> </u>	100	
	!			08,10,12, 15,16	1	200	<u> </u>
				03		300	
				06,07	<u> </u>	25	<u> </u>
Input <u>4</u> / capacitance	cI	V <sub>I</sub> = V <sub>CC</sub> or GND, f = 1 MHz  See 4.3.1c	   4 	   All 	   	10	   pF 
Output <u>4</u> / capacitance	co	  V <sub>IO</sub> = V <sub>CC</sub> or GND, f = 1 MHz  See 4.3.1c	   4 	   All 	   	12	   pF 
Read/write cycle	tavav	5/ 6/	   9,10,11	01	280		ns
time	,	· 	[	  02,03,16	90	<u> </u> 	
			 	   <u>04</u>	  150	<u> </u>	
				   <u>05</u>	  200		<u> </u> 
				   <u>15</u>	  120		<u> </u> 
			t t	  07	  170		.
			1	08,09	   45		<u> </u> 
				10,11	55		
				06,12,13	   70		
	1			14	   <b>3</b> 5		!

See footnotes at end of table.

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Test	  Symbol	Conditions <u>1</u> / <u>2</u> /	  Group A	Device	  _Limit	   Unit	
		$V_{SS} = 0 \text{ V}, 4.5 \text{ V} \leq V_{CS} \leq 5.5 \text{ V}$ -55°C $\leq T_{C} \leq +125$ °C unless otherwise specified	subgroups	types	   Min	Max	
Address access time	tAVQV	   <u>5</u> / <u>6</u> /	9,10,11	01		200	ns ns
				02,03,16	<u> </u>	90	.
				04	<u> </u>	150	
				05		200	
				07,15		120	
				08,09		45	
				10,11	<u> </u>	55	
				06,12,13		70	
			•	14		35	
Output hold after address change	†AVQX	5/ <u>6</u> /	9,10,11	15,16	0	<u> </u>	ns
4/				04,05 02,03,06,	10	<u> </u>	
				07,08-14	-		
Output enable to output active	toLQX	<u>5</u> / <u>6</u> /	9,10,11	01,07	10	 	ns
4/			 	02,03,06, 08,12,13	5   5		
			 	04,05,09,  11,14,15,  16	      0	4	 
Output enable access	t <sub>OLQV</sub>	<u>5</u> / <u>6</u> /	   9,10,11	01,07,15	 	80	ns
time			<u> </u> 	  02,03,16	 	65	
			ļ	04	<u> </u>	   60	
			<u> </u>	05	<u> </u>	   70	
			<u> </u>	08,09	<u> </u>	25	
				10,11		40	 
				06,12,13		 <u>  50</u>	
				<u> </u>  14	 	20	[ [

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Test	Symbol	Symbol   Conditions 1/2/   G		Device	Limit	Unit	
		$V_{SS} = 0 \text{ V}, 4.5 \text{ V} \leq V_{CS} \leq 5.5 \text{ V}$ -55°C $\leq T_{C} \leq +125$ °C unless otherwise specified	subgroups	types	   Min 	   Max	
Chip enable to	t <sub>ELQX</sub>	   <u>5</u> / <u>6</u> /	9,10,11	01,07	10	<u> </u>	ns
output active <u>4</u> /		 		02,03,06,	   5 	   	
				04,05, 15,16	   0		
Chip enable access	  t <sub>ELQV</sub>	   <u>5</u> / <u>6</u> /	9,10,11	01	1	200	ns
time	 	 		02,03,16	1	90	
		 		04	1	150	   
				05	 	200	<u> </u>
				07,15	 	120	.
				08,09	<u> </u>	45	.
				10,11	<u> </u>	55	
	Ì			06,12,13		70	.
			<u> </u> 	14	<u> </u>	35	<u> </u>
Chip enable to output in high Z <u>4</u> /	<sup>t</sup> EHQZ	<u>5</u> / <u>6</u> /	9,10,11	01 02,03,07, 15,16	<u> </u> 	80     50	ns
			į	04,05		60	
	1		j I	08,09		25	
				10,11	l L	30	
				06,12,13	<u> </u>	35	 .
				14	<u> </u>	15	1
Write recovery time	   t   	   <u>5</u> / <u>6</u> / 	9,10,11	  02,03,04,  05,06,15,   <u>16</u>	   10 		ns
				09,11,14	   0		

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Test	Symbol	mbol   Conditions $1/2/$   G		Device	   Limit	   Unit	
			subgroups   	types	Min	Max	   
Chip enable to	t <sub>ELWH</sub>	<u>5</u> / <u>6</u> /	   9,10,11	01	200	<u> </u>	ns
end-of-write			<u> </u>	02,03,16	55	ļ Ļ	
				04	90		.ļ .ļ
				05,07	120	<u> </u>	.ļ
				06	45	<u> </u>	 .
				08,09,14	30	<u> </u>	.ļ
			<u> </u>	10-13	40	<u> </u>	 .
				15	70	<u> </u>	<u> </u>
Address valid to end-of-write	  tavwh	   <u>5</u> / <u>6</u> /	9,10,11	02,03, 12,13	65		ns
				04	  _100	1	
		 		05	   130	ļ 	.l
				15	  _105		 .
				06	   50		
				  08,09,14	   30		
				10,11	   45	i I	
				16	   80		Ĭ 
Address to WE setup	   tavwl	<u>5</u> / <u>6</u> /	9,10,11	02-06, 15,16	10		ns
time .		 	   	07,08,09, 11,14	     0	†   	
				   <u>10</u>	5	<u> </u>	
			<u> </u>	12,13	   15		<u> </u>
Address to ČE setup	   tavel	<u>5</u> / <u>6</u> /	9,10,11	01,07	0		ns

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Test	Symbol		  Group A	   Device	   <u>Limit</u>	   Unit	
			subgroups	types   	Min   Max		
Output enable to	t <sub>OHQZ</sub>	   <u>5</u> / <u>6</u> /	   9,10,11	   <u>01</u>	<u> </u>	   80	ns
output in high Z <u>4</u> /			 	02,03,		40	
				04,07	<u> </u>	50	
				05		60	
				08,09		25	
				10,11	<u> </u>	30	
				06,12,13		35	   
	1		<u> </u>	14		15	_
Write enable pulse width	t <sub>WLWH</sub>	<u>5</u> / <u>6</u> /	9,10,11	01	200	-	ns
			   	02,03,16	55	ļ	!   
				04	90	ļ	
				05,07	120	1	
				15	70	<u> </u>	   
				08,11	25	<u> </u> 	 
				12,13	40	<u> </u> 	
-			1	09,14	20		
Data setup to end-of-write	<sup>t</sup> DVWH	<u>5</u> / <u>6</u> /	9,10,11	01	80	<u> </u>	l   ns
end-or-write			 	02,03,06, 12,13,16	30		   
				04,07	50	<u> </u>	 
			<u> </u>	05	70		 
			<u> </u>	08,09	20	<u> </u>	
				10,11	25		!
				15	   35	1	 
			 	   14	15	}	 

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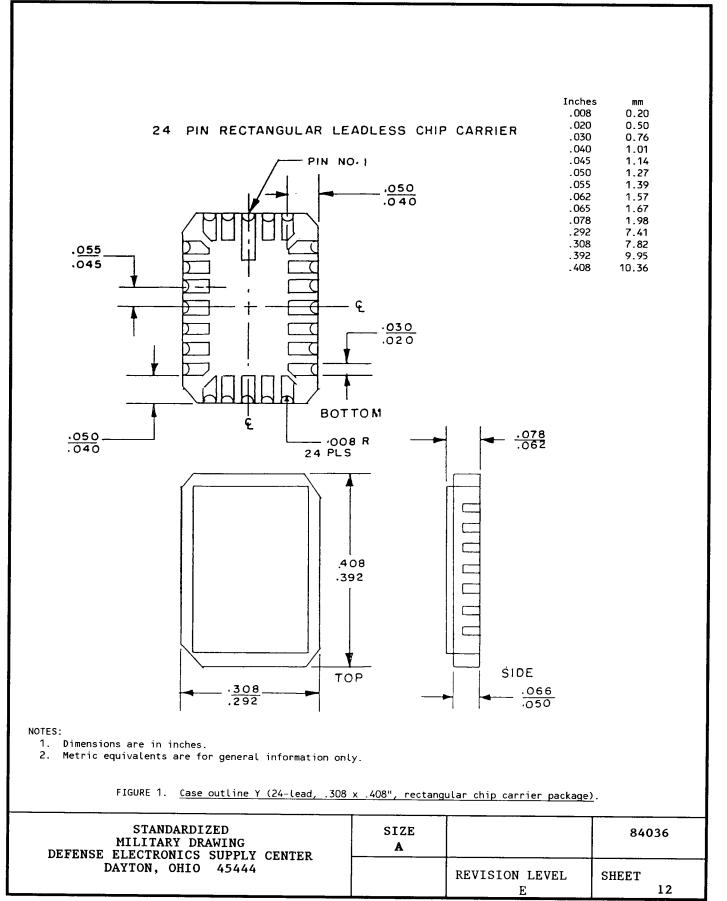
Test	Symbol			Device	Limit	Unit	
		$V_{SS} = 0 \text{ V}, 4.5 \text{ V} \leq V_{CG} \leq 5.5 \text{ V}$ $-55^{\circ}\text{C} \leq T_{C} \leq +125^{\circ}\text{C}$ unless otherwise specified	subgroups 	types	Min	Max	   
Data hold after end-of-write	twHDX	<u>5</u> / <u>6</u> /	9,10,11	01,06,07	10	<del> </del>	ns
end-of-write				02,03,04,	15		
				08,09,	0	<u> </u>	
	<u> </u>	1	1	10,12,13	5	<u> </u>	
Minimum chip-enable high time after	t <sub>EHEL</sub>	<u>5</u> / <u>6</u> /	9,10,11	01	80	1	ns
write				07	50	-	<u> </u>
Address <u>ho</u> ld time after CE low	tELAX	<u>5</u> / <u>6</u> /	9,10,11	01	50	<del> </del>	ns
arter to tow		1	<u> </u>	07	30		<u> </u>
Chip-enable pulse width during	t <sub>ELEH</sub>	<u>5</u> / <u>6</u> /	9,10,11	01	200	-	ns
write			<u> </u>	07	120	<del> </del>	<u> </u>
Write enable pulse setup time	twLEH	<u>5</u> / <u>6</u> /	9,10,11	01	200	<u> </u>	ns
Scrup Cime		1		02,03,16	55		
				04	90		.
				05,07	120		
				08	30	<u> </u>	
			1	12,13	40	<u> </u>	
			†	09,14	20	<u> </u>	
				11	25	<u> </u>	_
				   15	70		

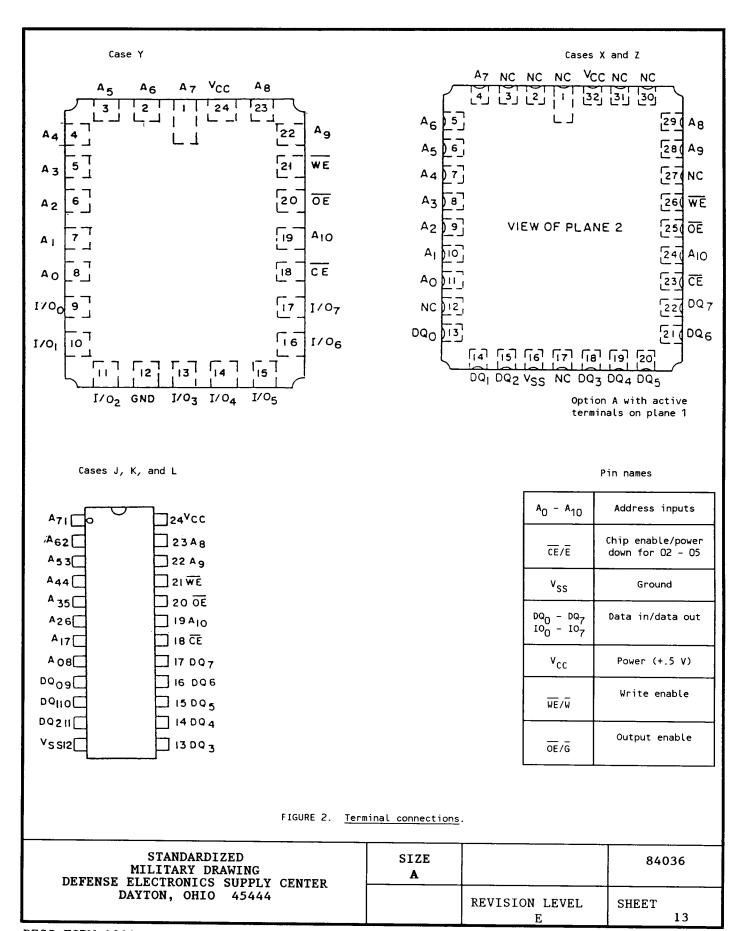
6/ For timing waveforms, see figure 6.

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 $<sup>\</sup>frac{1}{2}/$  All voltages referenced to V $_{SS}$  . Negative undershoots to a minimum of -0.3 V are allowed with a maximum of 20 ns pulse width.

Negative undershoots to a minimum of -0.3 V are allowed with a maximum of 20 ns pulse width.  $\frac{3}{4}$  / Tested initially, and after any design or process change which could affect these parameters.  $\frac{5}{4}$  AC measurements assume transition time  $\frac{4}{4}$  5 ns and input levels are from  $\frac{4}{4}$  to 3.0 V. Output load is specified on figure 5. Reference timing levels are at 1.5 V.







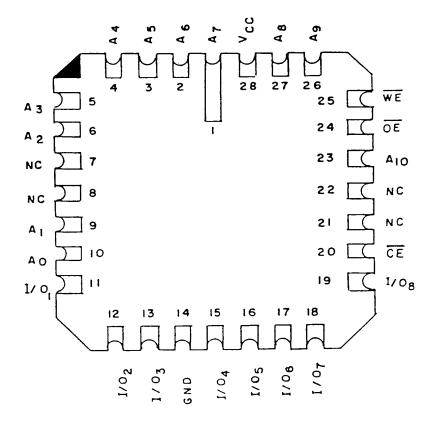


FIGURE 2. <u>Terminal connection</u>. - Continued

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# Device types 01 and 07 Read cycle

Time reference			Inputs		1	Function
	CE	WE	ŌĒ	Α	DQ	
-1	н	X	х	Х	Z	Memory disabled
0	4	Н	х	٧	Z	Cycle begins, addresses are latched
1	L	н	L	х	х	Output enabled
2	L	Н	L	х	V	Output valid
3	<b>A</b>	Н	х	х	v	Read accomplished
4	Н	х	х	х	Z	Prepare for next cycle (same as -1)
5	4	Н	х	V	Z	Cycle ends, next cycle begins (same as 0)

# Write cycle

Time reference		·	Inputs		1	Function
	CE	WE	ŌĒ	A	DQ	
-1	Н	х	Н	Х	х	Memory disabled
0	4	х	Н	V	х	Cycle begins, addresses are latched
1	L	L	Н	х	х	Write period begins
2	L	<b>A</b> ^	н	х	V	Data is written
3	\ <b>A</b> ^	н	Н	х	х	Write completed
4	Н	х	Н	х	х	Prepare for next cycle (same as -1)
5	4	х	н	V	х	Cycle ends, next cycle begins (same as O)

# Device types 02 - 06 and 08 - 16

CE	OE	WE	Mode	DQ
V <sub>IH</sub>	х	Х	Deselect	High Z
V <sub>IL</sub>	х	v <sub>IL</sub>	Write	D <sub>IN</sub>
v <sub>IL</sub>	VIL	v <sub>IH</sub>	Read	D <sub>OUT</sub>
VIL	v <sub>IH</sub>	v <sub>IH</sub>	Read	High Z

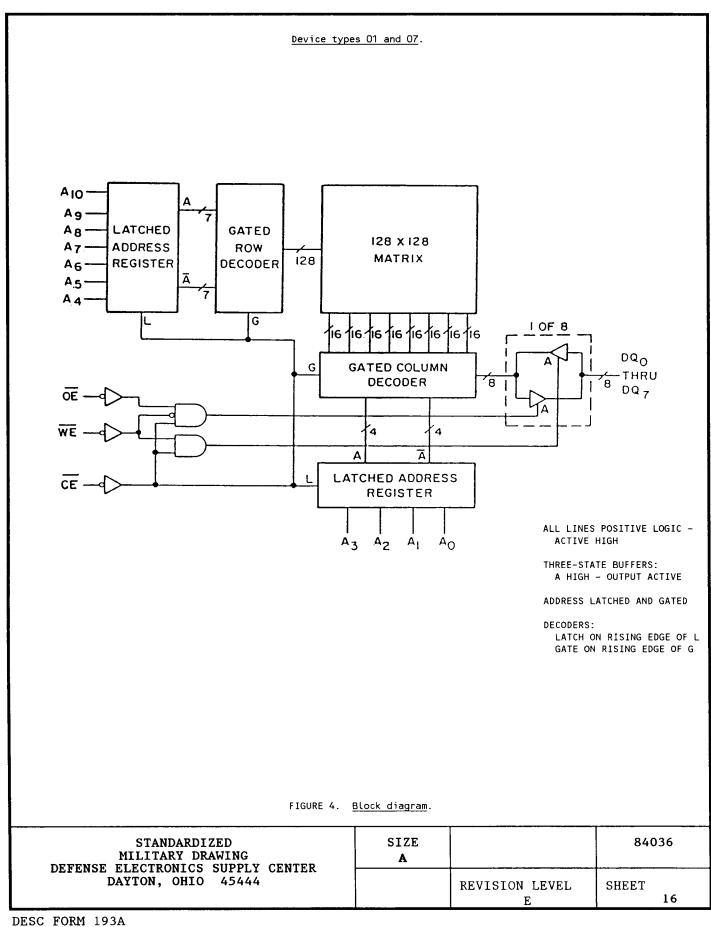
X = Don't care

# FIGURE 3. <u>Truth table</u>.

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### Device types 02 - 06 and 08 - 16

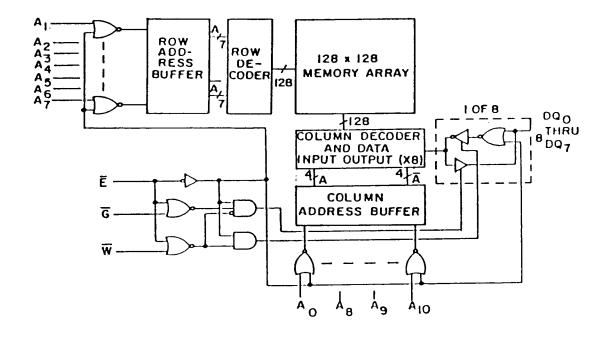
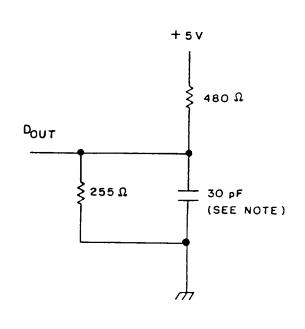
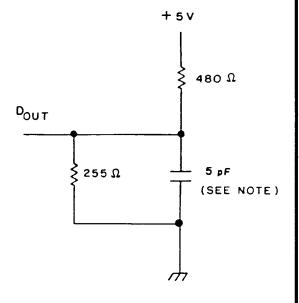


FIGURE 4. <u>Block diagram</u> - Continued.

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# <u>Circuit A or equivalent circuit</u>

For all other switching parameters.

# Circuit B or equivalent circuit

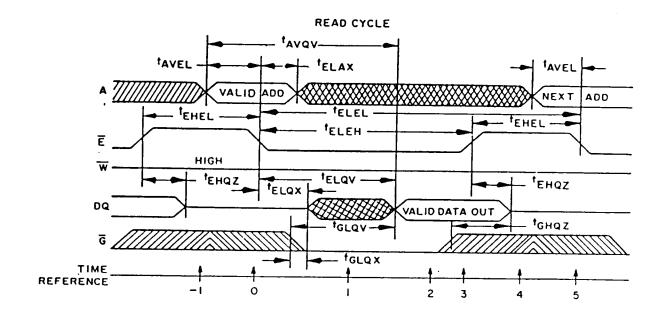
for  $t_{OLQX'}$   $t_{ELQX'}$   $t_{EHQZ'}$  and  $t_{OHQZ}$ .

NOTE:
1. Including scope and jig capacitance.

FIGURE 5. Output loading.

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FIGURE 5. Output Loading.
Device types 01 and 07

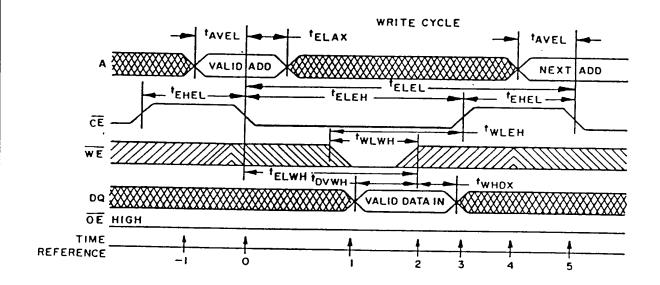


The address information is latched in the on chip registers on the falling edge of CE (t = 0), minimum address setup and hold time requirements must be met. After the required hold time, the address may change state without affecting device operation. During time (t = 1), the outputs become enabled but data is not valid until time (t = 2), WE must remain high throughout the read cycle. After the data has been read, CE may return high (t = 3). This will force the output buffers into a high impedance mode at time (t = 4).  $\overline{OE}$  is used to disable the output buffers when in a logical "1" state (t = -1, 0, 3, 4, 5). After (t = 4) time, the memory is ready for the next cycle.

FIGURE 6. Timing waveforms.

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### Device types 01 and 07



The write cycles is initiated on the falling edge of  $\overline{\text{CE}}$  (t = 0), which latches the address information in the on chip registers. If a write cycle is to be performed where the output is not to become active,  $\overline{\text{OE}}$  can be held high (<u>inactive</u>). Parameter  $t_{\text{DVHW}}$  and  $t_{\text{WHDX}}$  must be met for proper device operation regardless of  $\overline{\text{OE}}$ . If  $\overline{\text{CE}}$  and  $\overline{\text{OE}}$  fall before  $\overline{\text{WE}}$  falls (read mode), a possible bus conflict may exist. If  $\overline{\text{CE}}$  rises before  $\overline{\text{WE}}$  rises, reference data setup and hold times to the  $\overline{\text{CE}}$  rising edge. The write operation is terminated by the first rising edge of  $\overline{\text{WE}}$  (t = 2) or  $\overline{\text{CE}}$  (t = 3). After the minimum  $\overline{\text{CE}}$  high time ( $t_{\overline{\text{EHE}}}$ ), the next cycle may begin. If a series of consecutive write cycles are to be performed, the WE line may be held low until all desired locations have been written. In this case, data setup and hold times must be referenced to the rising of  $\overline{\text{CE}}$ .

FIGURE 6. Timing waveforms - Continued.

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# Device types 02 - 06 and 08 - 16

# ADDRESS TAVAV TELWH TWHAV WE TWLQZ TOVEH TOVEH TAVAV TAV

NOTE:  $\overline{G}$  is low throughout write cycle.

To write, addresses must be stable,  $\overline{\text{CE}}$  low and  $\overline{\text{WE}}$  falling low for a period no shorter than tylyh. Data is in referenced with the rising edge of  $\overline{\text{WE}}$  or  $\overline{\text{CE}}$  whichever occurs first (tpvyh and tyhpx). While addresses are changing,  $\overline{\text{WE}}$  must be high. When  $\overline{\text{WE}}$  falls low, the I/O pins are still in the output state for a period of tyho and input data of the opposite phase to the outputs must not be applied (bus contention). If  $\overline{\text{CE}}$  transitions low simultaneously with  $\overline{\text{WE}}$  line transitioning low or after the  $\overline{\text{WE}}$  transition, the output will remain in a high impedance state.  $\overline{\text{OE}}$  is held continuously low.

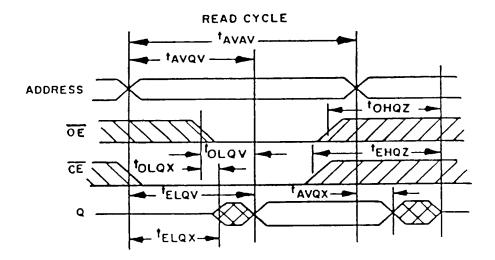
FIGURE 6. <u>Timing waveforms</u> - Continued.

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# Device types 02 - 06 and 08 - 16



NOTE: W is high for a read cycle.

Addresses must remain stable for the duration of the read cycle. To read,  $\overline{\text{OE}}$  and  $\overline{\text{CE}}$  must be  $\leq$  V $_{\text{IL}}$  and  $\overline{\text{WE}}$   $\geq$  V $_{\text{IH}}$ . The output buffers can be controlled independently by  $\overline{\text{OE}}$  while  $\overline{\text{CE}}$  is low. To execute consecutive read cycles,  $\overline{\text{CE}}$  may be tied low continuously until all desired locations are accessed. When  $\overline{\text{CE}}$  is low, addresses must be driven by stable logic levels and must not be in the high impedance stated.

FIGURE 6. Timing waveforms - Continued.

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TABLE II. <u>Electrical test requirements</u>.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	
Final electrical test parameters	1*, 2, 3, 7, 8,
(method 5004)	9, 10, 11
Group A test requirements	1, 2, 3, 4, 7, 8
(method 5005)	9, 10, 11
Groups Ç and D end-point	
electrical parameters	1, 7, 9
(method 5005)	

<sup>\*</sup> PDA applies to subgroup 1.

# 4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
  - a. Burn-in test, method 1015 of MIL-STD-883.
    - (1) Test condition D using the circuit submitted with the certificate of compliance (see 3.6 herein).
    - (2)  $T_A = +125$ °C, minimum.
  - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
  - 4.3.1 Group A inspection.
    - a. Test shall be as specified in table II herein.
    - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
    - c. Subgroup 4 (C<sub>IN</sub> and C<sub>OUT</sub> measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance. Sample size is 15 devices with no failures, and all input and output terminals tested.
    - d. Subgroup 7 and 8 tests shall include verification of the truth table.
  - 4.3.2 Groups C and D inspections.
    - a. End-point electrical parameters shall be as specified in table II herein.
    - b. Steady-state life test conditions, method 1005 of MIL-STD-883.
      - (1) Test condition D using the circuit submitted with the certificate of compliance (see 3.6 herein).
      - (2)  $T_A = +125$ °C, minimum.
      - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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- PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
- 6. NOTES
- 6.1 <u>Intended use.</u> Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
  - 6.2 Replaceability. Replaceability is determined as follows:
    - a. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
    - b. When a QPL source is established, the part numbered device specified in this drawing will be replaced by the microcircuit identified as part number M38510/2910XB--.
- 6. <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6047.
- 6.5 <u>Comments</u>. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone (513) 296-5377.
- 6.6 <u>Approved sources of supply</u>. Approved sources of supply are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-ECS.

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